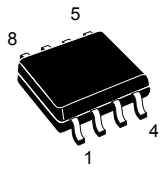
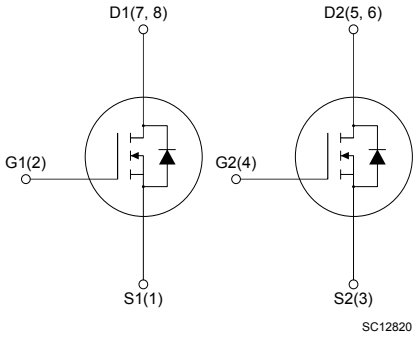
STS1DNC45

Datasheet

Dual N-channel 450 V, 4.1 Ω typ., 0.4 A SuperMESH Power MOSFET in a SO-8 package



SO-8



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STS1DNC45	450 V	4.5 Ω	0.4 A

- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitance

Application

- Switch mode low-power supplies (SMPS)
- DC-DC converters
- Low power, low-cost CFL (compact fluorescent lamps)
- Low-power battery chargers

Description

This high voltage device is an N-channel Power MOSFET developed using the SuperMESH technology by STMicroelectronics, an optimization of the well-established PowerMESH. In addition to a significant reduction in on-resistance, this device is designed to ensure a high level of dv/dt capability for the most demanding applications.

Product status link
STS1DNC45

Product summary	
Order code	STS1DNC45
Marking	1DC45)
Package	SO-8
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	450	V
V_{DGR}	Drain-gate voltage (R_{GS} = 20 kΩ)	450	V
V_{GS}	Gate-source voltage	±30	V
I_D	Drain current (continuous) at T_C = 25 °C	0.4	A
	Drain current (continuous) at T_C = 100 °C	0.25	
I_{DM}(1)	Drain current (pulsed)	1.6	A
P_{TOT}	Total power dissipation at T_A = 25 °C, dual operation	1.6	W
	Total power dissipation at T_A = 25 °C, single operation	2	
dv/dt(2)	Peak diode recovery voltage slope	3	V/ns
T_{stg}	Storage temperature range	-65 to 150	°C
T_J	Operating junction temperature range		°C

1. *Pulse width limited by safe operating area.*
2. *I_{SD} ≤ 0.4 A, di/dt ≤ 100 A/µs, V_{DD} < $V_{(BR)DSS}$.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJA}	Thermal resistance, junction-to-ambient, single operation	62.5	°C/W
	Thermal resistance, junction-to-ambient, dual operation	78	

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width is limited by T_J max.)	0.4	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	30	mJ

2 Electrical characteristics

T_C = 25 °C unless otherwise specified.

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 250 µA	450			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 450 V			1	µA
		V_{GS} = 0 V, V_{DS} = 450 V, T_C = 125 °C(1)			50	
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±30 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2.3	3	3.7	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 10 V, I_D = 0.5 A		4.1	4.5	Ω

1. *Specified by design, not tested in production.*

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs}(1)	Forward transconductance	V_{DS} = 25 V, I_D = 0.5 A	-	1.1		S
C_{iss}	Input capacitance	V_{DS} = 25 V, f = 1 MHz, V_{GS} = 0 V	-	160		pF
C_{oss}	Output capacitance		-	27.5		pF
C_{rss}	Reverse transfer capacitance		-	4.7		pF
Q_g	Total gate charge	V_{DD} = 360 V, I_D = 1.5 A, V_{GS} = 0 to 10 V (see Figure 16. Test circuit for gate charge behavior)	-	7	10(2)	nC
Q_{gs}	Gate-source charge		-	1.3		nC
Q_{gd}	Gate-drain charge		-	3.2		nC

1. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%.*
2. *Specified by design, not tested in production.*

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 225 V, I_D = 0.5 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 15. Test circuit for resistive load switching times and Figure 20. Switching time waveform)	-	6.7	-	ns
t_r	Rise time		-	4	-	ns
$t_{r(off)}$	Turn-off rise time	V_{DD} = 360 V, I_D = 1.5 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 17. Test circuit for inductive load switching and diode recovery times)	-	8.5	-	ns
t_f	Fall time			12		ns
t_c	Cross-over time		-	18	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		0.4	A
I_{SDM}(1)	Source-drain current (pulsed)		-		1.6	A
V_{SD}(2)	Forward on voltage	I_{SD} = 0.4 A, V_{GS} = 0 V	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 0.4 A, di/dt = 100 A/µs	-	225		ns
Q_{rr}	Reverse recovery charge	V_{DD} = 100 V, T_J = 150 °C	-	530		nC
I_{RRM}	Reverse recovery current	(see Figure 17. Test circuit for inductive load switching and diode recovery times)	-	4.7		A

1. *Pulse width is limited by safe operating area.*
2. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

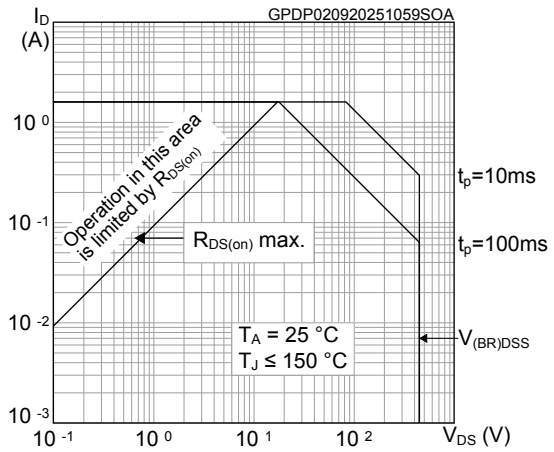


Figure 2. Normalized transient thermal impedance

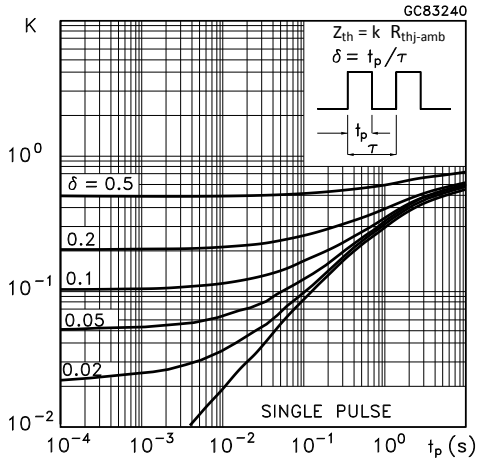


Figure 3. Typical output characterisics

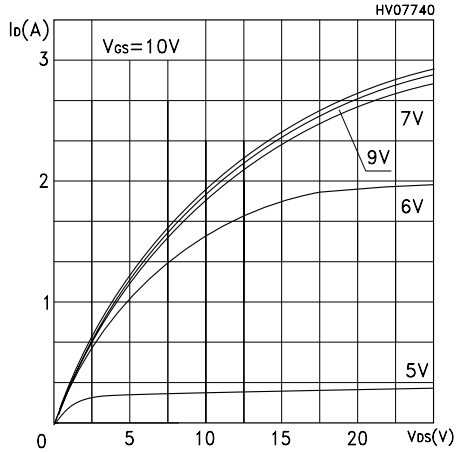


Figure 4. Typical transfer characteristics

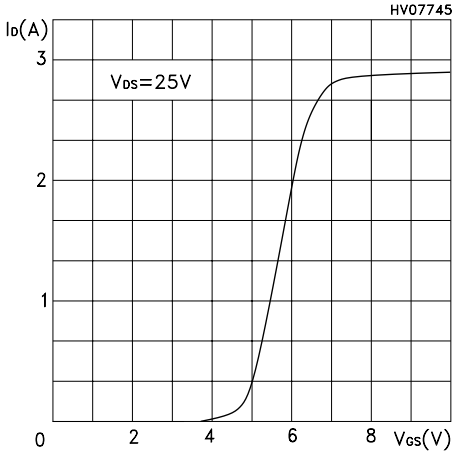


Figure 5. Typical transconductance characteristics

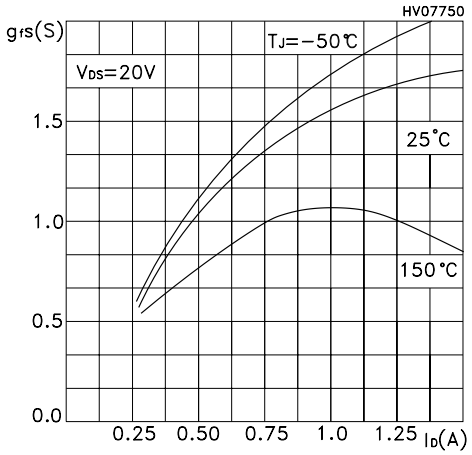


Figure 6. Typical gate charge characteristics

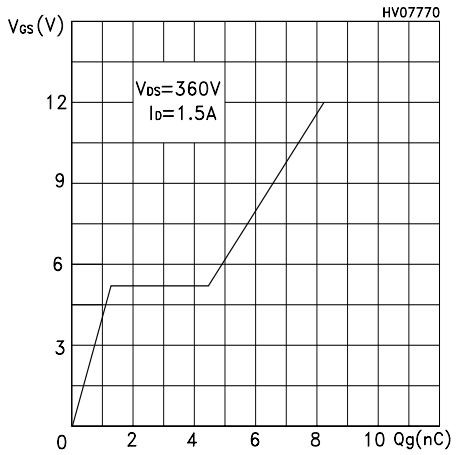


Figure 7. Typical capacitance characteristics

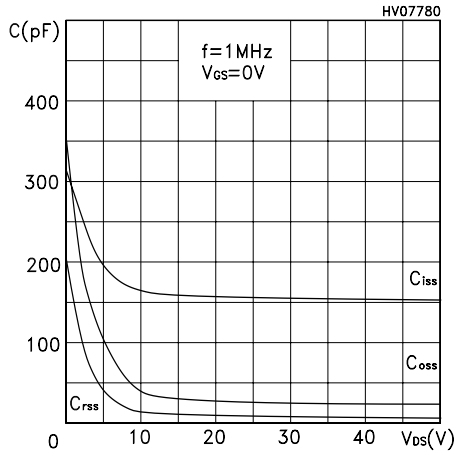


Figure 8. Typical drain-source on-resistance

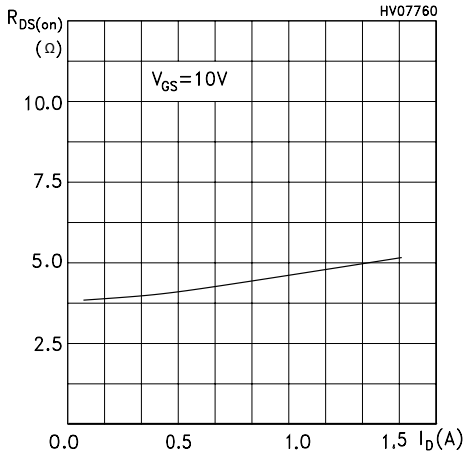


Figure 9. Normalized breakdown voltage vs temperature

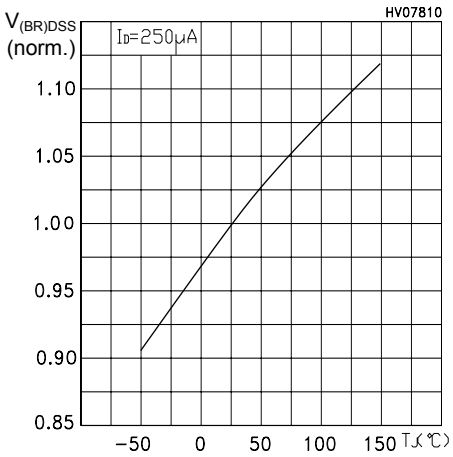


Figure 10. Normalized gate threshold vs temperature

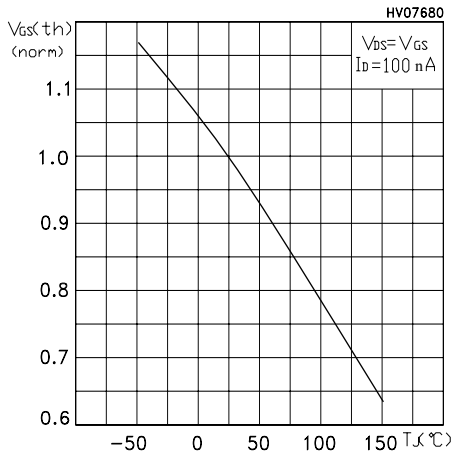


Figure 11. Normalized on-resistance vs temperature

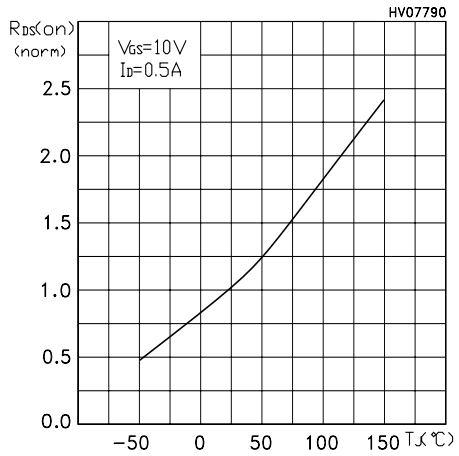


Figure 12. Typical reverse diode forward characteristics

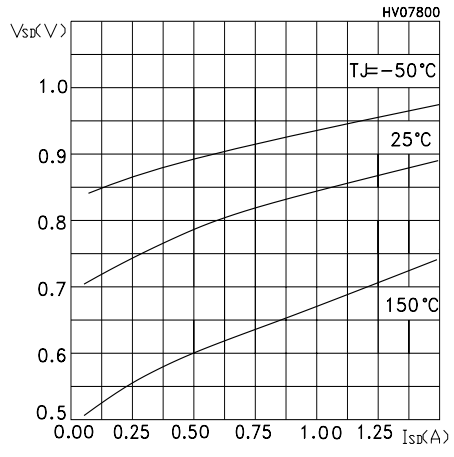


Figure 13. Maximum I_D current vs T_C

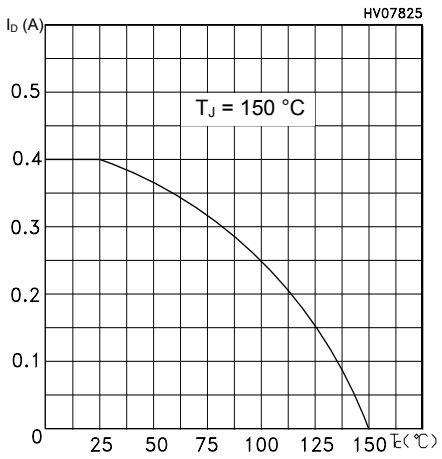
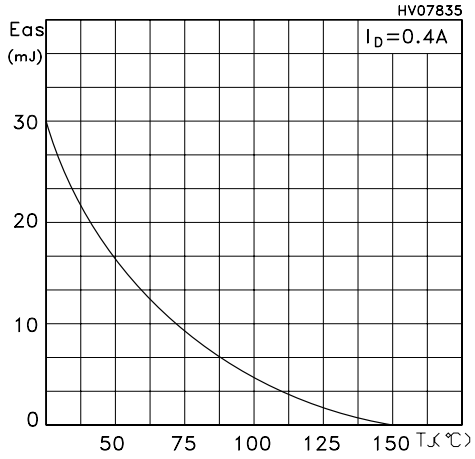
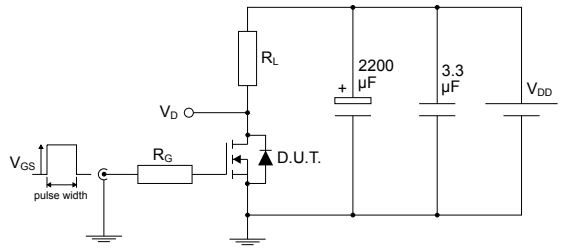


Figure 14. Maximum avalanche energy vs temperature



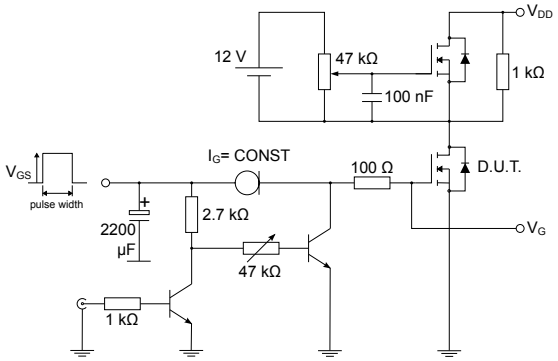
3 Test circuits

Figure 15. Test circuit for resistive load switching times



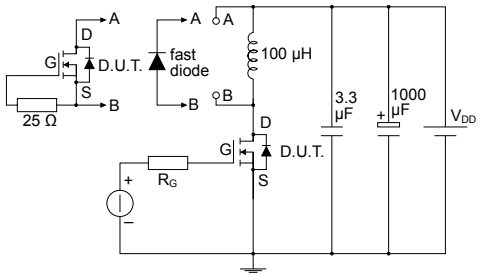
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Figure 16. Test circuit for gate charge behavior



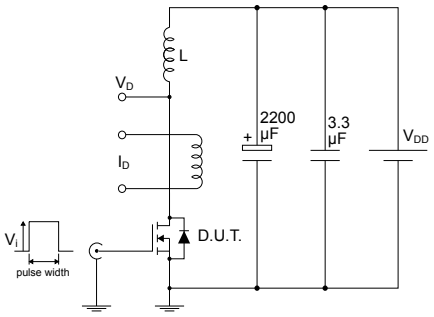
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Figure 17. Test circuit for inductive load switching and diode recovery times



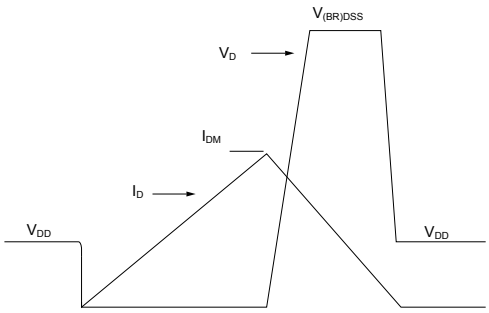
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Figure 18. Unclamped inductive load test circuit



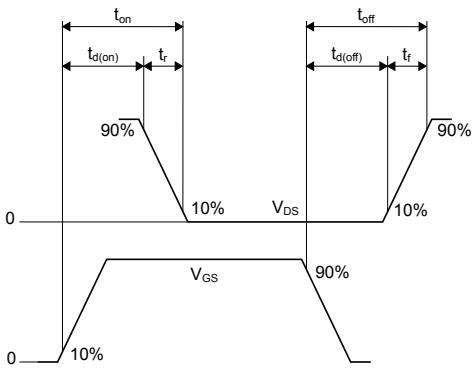
AM01471v1

Figure 19. Unclamped inductive waveform



AM01472v1

Figure 20. Switching time waveform



AM01473v1

4 Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 SO-8 package information

Figure 21. SO-8 package outline

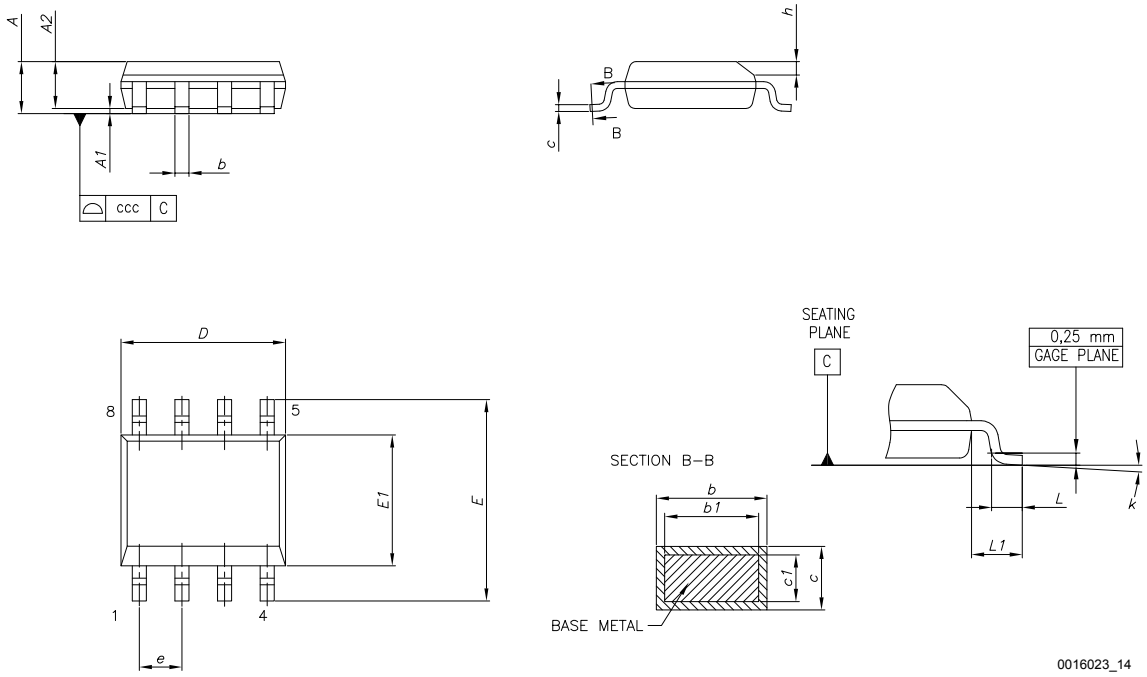
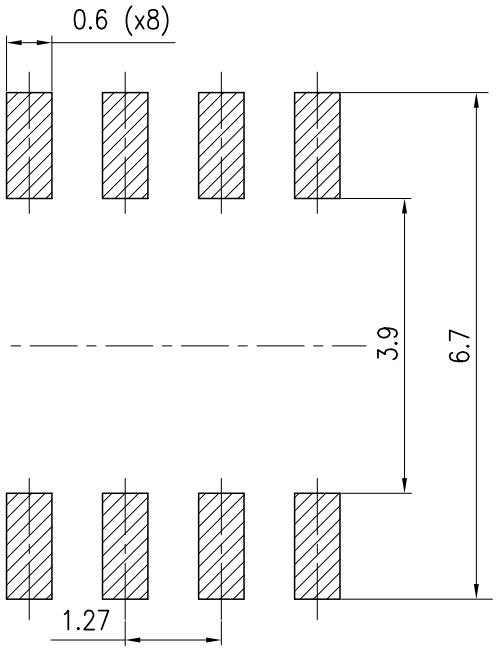


Table 8. **SO-8 mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A			1.75
A1	0.10		0.25
A2	1.25		
b	0.31		0.51
b1	0.28		0.48
c	0.10		0.25
c1	0.10		0.23
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e		1.27	
h	0.25		0.50
L	0.40		1.27
L1		1.04	
L2		0.25	
k	0°		8°
ccc			0.10

Figure 22. **SO-8 recommended footprint (dimensions are in mm)**



4.2 SO-8 packing information

Figure 23. **SO-8 tape and reel dimensions**

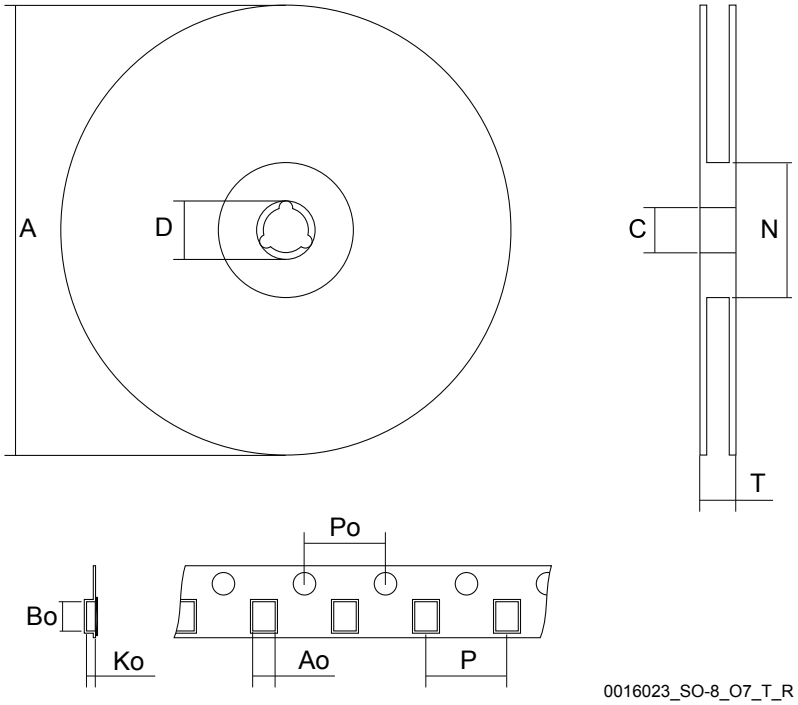


Figure 24. **Tape orientation**

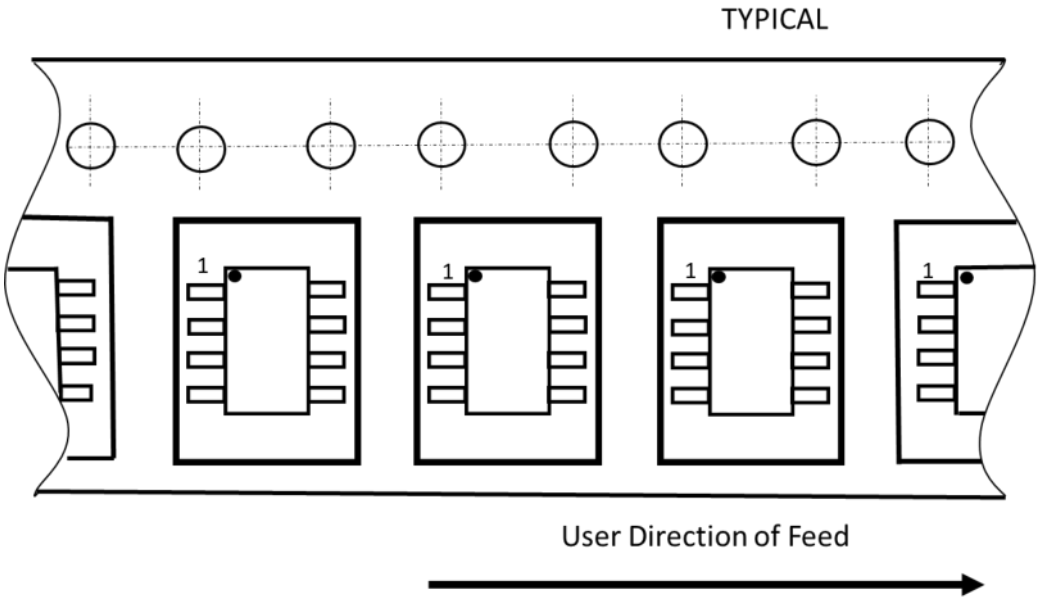


Table 9. **SO-8 tape and reel mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A		-	330
C	12.8		13.2
D	20.2		
N	60		
T			22.4
Ao	6.5		6.7
Bo	5.4		5.6
Ko	2.0		2.2
Po	3.9		4.1
P	7.9		8.1

Revision history

Table 10. **Document revision history**

Date	Revision	Changes
16-Sep-2025	3	Updated Figure 1. Safe operating area. Updated Section 4: Package information. Minor text changes.

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